

**1. Material**            Substrate        GaAs (N Type)  
                              Epitaxial Layer   GaAlAs (P/N Type)

**2. Electrode**        N(Cathode) Side Gold Alloy  
                              P(Anode) Side Gold Alloy

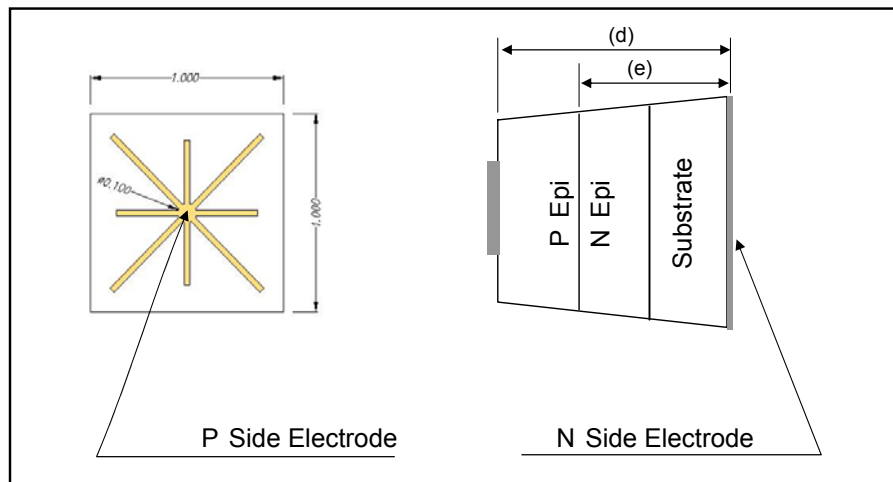
**3. Electro-Optical Characteristics**

Parameter	Symbo	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_F$		1.35	1.5	V	IF=350mA
Reverse Voltage	$V_R$	5			V	IR=10uA
Radiant Power	$P_O$	12	17		mW	IF=350mA
Wavelength	$\lambda_P$		940		nm	IF=20mA
	$\Delta\lambda$		45		nm	IF=20mA

※ Note : LED Chip is mounted on TO-18 gold header without resin coating.

**4. Mechanical Data**

(a) Emission Area	-----	39.0mil x	39.0mil
(b) Bottom Area	-----	40.0mil x	40.0mil
(c) Bonding Pad	-----	100um	
(d) Chip Thickness	-----	11mil	
(e) Junction Height	-----	6.7mil	



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